

Dual P-Channel MOSFET

-60V, -12A, $68m\Omega$

FEATURES

- Fast switching
- · Low thermal resistance package
- Low profile package
- Pb-free plating
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition

- Power Supply
- Motor Control

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
$V_{ extsf{DS}}$		-60	V	
$R_{DS(on)}$	V _{GS} = -10V	68	0	
(max)	$V_{GS} = -4.5V$	110	mΩ	
Q_g		16.4	nC	









Gate 1

Pin 1

Gate 2

Pin 2

Pin 3

Pin 3

Pin 4

Pin 5,6

Dual P-Channel MOSFET

Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$	l _D	-12	А	
Continuous Drain Current	T _C = 100°C		-8		
Pulsed Drain Current (Note 2)		I _{DM}	-48	Α	
Total Power Dissipation @ T _C = 25°C		P_{DTOT}	3.5	W	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	7.2	mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	12	Α	
Operating Junction and Storage Temperature Range		T_J, T_STG	- 55 to +150	°C	

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction to Case Thermal Resistance	R _{eJC}	4.5	°C/W	
Junction to Ambient Thermal Resistance	R_{\ThetaJA}	85	°C/W	

Notes: R_{eJA} is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{eJA} is guaranteed by design while R_{eCA} is determined by the user's board design. R_{eJA} shown below for single device operation on FR-4 PCB in still air





ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)		1			•	1
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV _{DSS}	-60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	$V_{GS(TH)}$	-1.2	-1.6	-2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -60V, V_{GS} = 0V$	I _{DSS}			-1	μΑ
	V _{DS} = -48V, Tc = 125 ^o C				-10	
Drain-Source On-State Resistance	$V_{GS} = -10V, I_D = -6A$	$R_{DS(on)}$		54	68	mΩ
	$V_{GS} = -4.5V, I_D = -3A$			90	110	
Forward Transconductance	$V_{DS} = -10V, I_{D} = -6A$	g _{fs}		8.5		S
Dynamic (Note 5)				•	•	
Total Gate Charge	$V_{DS} = -30V, I_{D} = -6A,$ $V_{GS} = -10V$	Q_g		16.4		
Gate-Source Charge		Q_gs		2.8		nC
Gate-Drain Charge		Q_{gd}		3.6		
Input Capacitance		C _{iss}		870		
Output Capacitance	$V_{DS} = -30V, V_{GS} = 0V,$	C _{oss}		70		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		42		1
Switching (Note 6)	-					1
Turn-On Delay Time		t _{d(on)}		8.3		
Turn-On Rise Time	$V_{DD} = -30V, I_{D} = -1A,$	t _r		42.4		
Turn-Off Delay Time	$R_{GEN} = 6\Omega$	t _{d(off)}		64.6		ns
Turn-Off Fall Time		t _f		16.4		
Source-Drain Diode (Note 4)				•	•	
Maximum Continuous Drain-Source		1			-12	Α
Diode Forward Current	Integral reverse diode	I _S			-12	A
Maximum Pulse Drain-Source	in the MOSFET	I _{SM}			-48	Α
Diode Forward Current), ov. 1	_				
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = -1A$	V_{SD}			-1	V

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 0.1 mH, $I_{AS} = -12 A$, $V_{DD} = -25 V$, $R_G = 25 \Omega$, Starting $T_J = 25 ^{\circ} C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.



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ORDERING INFORMATION (EXAMPLE)

PART NO.	PACKAGE	PACKING
TSM680P06DPQ56 RLG	PDFN56 Dual	2,500pcs / 13"Reel

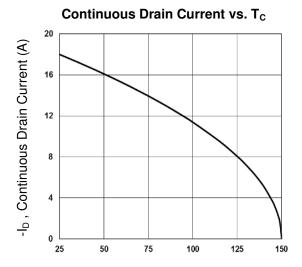
Note:

- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition

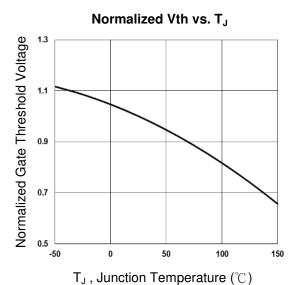


CHARACTERISTICS CURVES

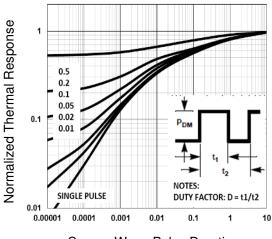
(T_C = 25°C unless otherwise noted)



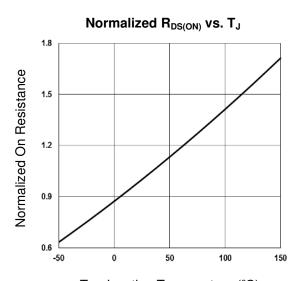
T_C, Case Temperature (°C)



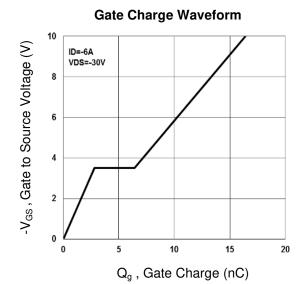
Normalized Transient Impedance



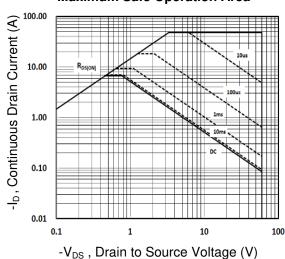
Square Wave Pulse Duration



T_J , Junction Temperature (°C)



Maximum Safe Operation Area

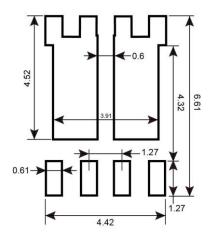




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

PDFN56 Dual 4.90 ±0.10 3.81 ±0.20 0.51 ±0.10 3.58 ±0.20 6.00 ±0.10 5.75 ±0.05 1.10 (Min) 0.61 ±0.10 0.13 ±0.07 1.27 (REF) 0.41 ±0.10 1.00 ±0.10 0.04 (REF

SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan **P** =Feb **Q** =Mar

R =Apr

S =May T =Jun **U** =Jul

V =Aug

W =Sep **X** =Oct

Y =Nov

Z =Dec

L = Lot Code $(1\sim9, A\sim Z)$



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